1200V/5.5mΩ Half Bridge SiC MOSFET Module

Description

The DFS05HF12EZR1 is a Half Bridge SiC MOSFET half bridge Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Solar Inverter, UPS, Fuel cell-DC/DC converter, Energy storage Systems.



Features

- Blocking voltage:1200V
- $5.5 \text{m}\Omega \text{ R}_{ds(on)}$
- Low Switching Losses
- 175°C maximum junction temperature
- Si₃N₄ DBC
- Thermistor inside

Applications

- Solar inverter Systems
- Fuel cell-DC/DC converter
- Uninterruptible Power Supplier
- Energy Storage Systems

Circuit diagram

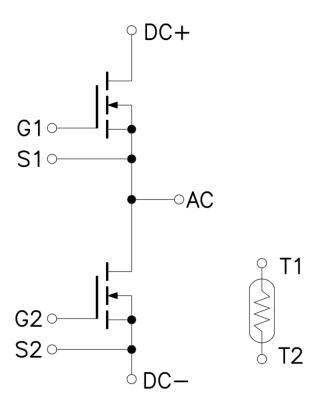


Figure 1. Out drawing & circuit diagram for DFS05HF12EZR1

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Pin Configuration and Function Description

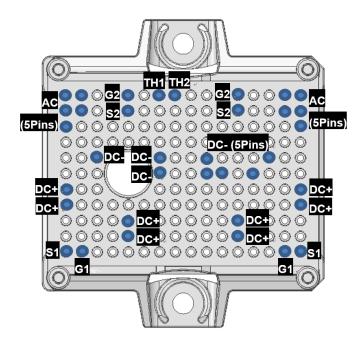


Figure 2. Pin configuration

PIN No.	Symbol	Description	
1-5(5pins)	AC	Output terminal of half bridge	
6	S2	Low side source signal terminal	
7	G2	Low side gate signal terminal	
8	TH1	Thermistor connection 1	
9	TH2	Thermistor connection 2	
10	S2	Low side source signal terminal	
11	G2	Low side gate signal terminal	
12-16(5pins)	AC	Output terminal of half bridge	
17-24(8pins)	DC –	DC – Bus connection	
25-32(8pins)	DC +	DC + Bus connection	
33	G1	High side gate signal terminal	
34	S1	High side source signal terminal	
35	G1	High side gate signal terminal	
36	S1	High side source signal terminal	

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f=50Hz, t=1min	3.4	kV
	Terminal to Terminal	5	mm
Clearance	Terminal to Heatsink	10	mm
C	Terminal to Terminal	6.3	mm
Creepage distance	Terminal to Heatsink	12.7	mm
Comparative Tracking Index	-	600	-



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Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short	1200	V
V _{GSS}	Gate-Source Voltage(+)	D-S Short	21	V
V _{GSS}	Gate-Source Voltage(-)	D-S Short	-2	V
V _{GSSSurge}	G-S Voltage(t _{surge} <300nsec)	D-S Short, Note1	-6 to 23	V
I_{DS}	DC Continuous Drain Current	T _f =75°C, Note2	200	A
I _{SD}	Source (Body diode) Current	T _f =75°C, with ON signal	200	A
I_{DP}	Drain Pulse Current, Peak	Less than 1ms, Note3	400	A
Tj	junction temperature	-	-40 to 175	°C
T _{stg}	Storage temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, 0V/+18V.

Note2: Case temperature(Tc) is defined on the surface of base plate just under the chips.

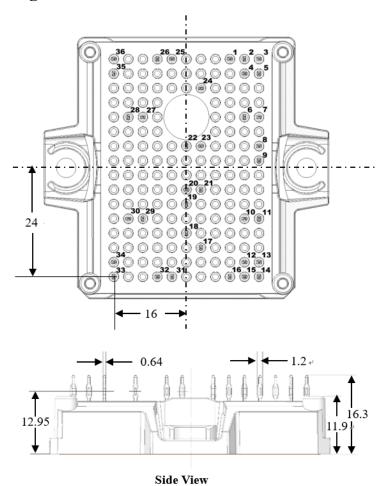
Note3: Pulse width limited by maximum junction temperature

NTC characteristics

Crymbal	Parameter	Condition	Value			Unit
Symbol			Min.	Тур.	Max.	Unit
R ₂₅	Resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	$T_C = 100$ °C, $R_{100} = 493\Omega$	5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-value	R2 =R25 exp [B _{25/50} (1/T2 - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R2 =R25 exp [B _{25/80} (1/T2 - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R2 =R25 exp [B _{25/100} (1/T2 - 1/(298,15 K))]	-	3433	-	K

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Package dimensions



Pin	X	Y
1	25,6	48
2	28,8	48
3	32	48
4	28,8	44,8
5	32	44,8
6	28,8	35,2
7	32	35,2
8	32	28,8
9	32	25,6
10	28,8	12,8
11	32	12,8
12	28,8	3,2
13	32	3,2
14	32	0
15	28,8	0
16	25,6	0
17	19,2	6,4
18	16	9,6
19	16	16
20	16	19,2
21	19,2	19,2
22	16	28,8
23	19,2	28,8
24	19,2	41,6
25	12,8	48
26	9,6	48
27	6,4	35,2
28	3,2	35,2
29	6,4	12,8
30	3,2	12,8
31	12,8	0
32	9,6	0
33	0	0
34	0	3,2
35	0	44,8
36	0	48

Unit: mm



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Editing record:

Version	Content	Data
A	First edition	2022.03.02

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